

# TIP35CW TIP36CW

## Complementary Silicon High Power Transistors

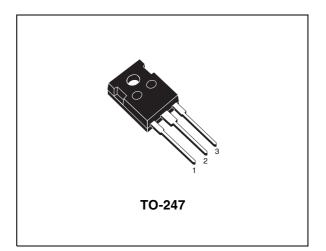
## Features

 STMicroelectronics PREFERRED SALESTYPES

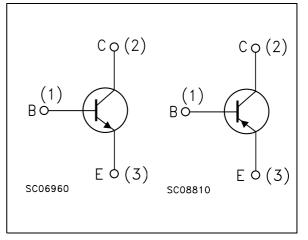
## Description

The dev ice is a s ilicon E pitaxial-Base NPN transistor mounted in TO-247 plastic package. It is i ntentend for u se i n p ower am plifier and switching applications.

The complementary PNP type is TIP36CW.



## **Internal Schematic Diagram**



## **Order Codes**

Part Number	Marking	Package	Packing
TIP35CW	TIP35C W	TO-247	Tube
TIP36CW	TIP36C W	TO-247	Tube

# 1 A bsolute Maximum Ratings

Table 1. Absolute Maximum Rating	g
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Symbol	Parameter		Value	Unit
	NPN		TIP35CW	
		PNP	TIP36CW	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		100	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		100	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		5V	
۱ <sub>C</sub>	Collector Current		25	А
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5ms)		50	А
I <sub>B</sub>	Base Current		5	А
P <sub>tot</sub>	Total Dissipation at $T_c = 25^{\circ}C$		125	W
T <sub>stg</sub>	Storage Temperature		-65 to 150	°C
TJ	Max. Operating Junction Temperature		150	°C

Note: For PNP types voltage and current values are negative.

#### Table 2.Thermal Data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal Resistance Junction-Case Max	1	°C/W

## 2 El ectrical Characteristics

Symbol	Parameter	Test Conc	litions	Min.	Тур.	Max.	Unit
I <sub>CEO</sub>	Collector Cut-off Current $(I_B = 0)$	V <sub>CE</sub> = 60 V				1	mA
I <sub>EBO</sub>	Emitter Cut-off Current $(I_{C} = 0)$	V <sub>EB</sub> = 5 V				1	mA
ICES	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = Rated V <sub>CEO</sub>	,			0.7	mA
V <sub>CEO(SUS)</sub> Note: 1	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 30 mA		100			V
h <sub>FE</sub> Note: 1	DC Current Gain	I <sub>C</sub> = 1.5 A I <sub>C</sub> = 15 A	V <sub>CE</sub> = 4 V V <sub>CE</sub> = 4 V	25 10		50	
V <sub>CE(sat)</sub> Note: 1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 15 A I <sub>C</sub> = 25 A	l <sub>B</sub> = 1.5 A l <sub>B</sub> = 5 A			1.8 4	V V
V <sub>BE(on)</sub> Note: 1	Base-Emitter Voltage	I <sub>C</sub> = 15 A I <sub>C</sub> = 25 A	V <sub>CE</sub> = 4 V V <sub>CE</sub> = 4 V			2 4	V V
f <sub>T</sub>	Transition Frequency	$I_{\rm C} = 1$ A $V_{\rm CE} = 10$	OV f = 1 MHz	ЗM			Hz
h <sub>fe</sub>	Small Signall Current Gain	$I_{C} = 1 A V_{CE} = 10$	OV f = 1 MHz	25			

Table 3.Electrical Characteristics ( $T_{case} = 25^{\circ}C$ ; unless otherwise specified)

Note: 1 Pulsed duration =  $300 \,\mu s$ , duty cycle  $\leq 1.5\%$ .

2 For PNP types voltage and current values are negative.

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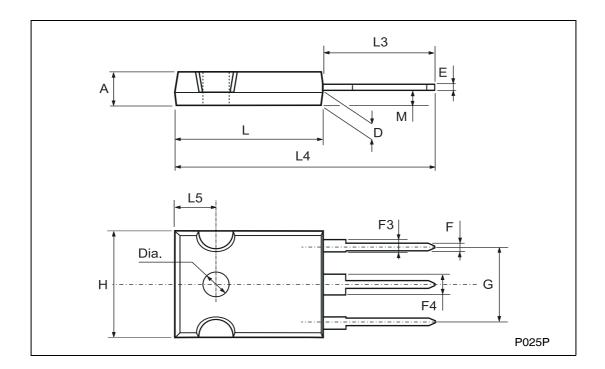
## 3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.		mm			inch		
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		5.3	0.185		0.209	
D	2.2		2.6	0.087		0.102	
E	0.4		0.8	0.016		0.031	
F	1		1.4	0.039		0.055	
F3	2		2.4	0.079		0.094	
F4	3		3.4	0.118		0.134	
G		10.9			0.429		
н	15.3		15.9	0.602		0.626	
L	19.7		20.3	0.776		0.779	
L3	14.2		14.8	0.559		0.582	
L4		34.6			1.362		
L5		5.5			0.217		
М	2		3	0.079		0.118	

#### **TO-247 MECHANICAL DATA**



# 4 R evision History

Date	Revision	Changes
02-Nov-2005	1	Initial release.
12-Dec-2005	2	Added the ECOPACK Label.



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